

Sample &

Buy





Support &

29

#### LM2621

SNVS033D - MAY 2004 - REVISED NOVEMBER 2015

# LM2621 Low Input Voltage, Step-Up DC-DC Converter

Technical

Documents

### 1 Features

- Small VSSOP8 Package (Half the Footprint of Standard 8-Pin SOIC Package)
- 1.09-mm Package Height
- Up to 2-MHz Switching Frequency
- 1.2-V to 14-V Input Voltage
- 1.24-V to 14-V Adjustable Output Voltage
- Up to 1A Load Current
- 0.17-Ω Internal MOSFET
- Up to 90% Regulator Efficiency
- 80-µA Typical Operating Current
- < 2.5-µA Specified Supply Current In Shutdown</li>

## 2 Applications

- PDAs, Cellular Phones
- 2-Cell and 3-Cell Battery-Operated Equipment
- PCMCIA Cards, Memory Cards
- Flash Memory Programming
- TFT/LCD Applications
- 3.3-V to 5.0-V Conversion
- GPS Devices
- Two-Way Pagers
- Palmtop Computers
- Hand-Held Instruments

## **3** Description

Tools &

Software

The LM2621 is a high efficiency, step-up DC-DC switching regulator for battery-powered and low input voltage systems. It accepts an input voltage between 1.2 V and 14 V and converts it into a regulated output voltage. The output voltage can be adjusted between 1.24 V and 14 V. It has an internal 0.17- $\Omega$  N-Channel MOSFET power switch. Efficiencies up to 90% are achievable using the LM2621.

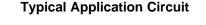
The high switching frequency (adjustable up to 2 MHz) of the LM2621 allows for tiny surface mount inductors and capacitors. Because of the unique constant-duty-cycle gated oscillator topology very high efficiencies are realized over a wide load range. The supply current is reduced to 80  $\mu$ A because of the BiCMOS process technology. In the shutdown mode, the supply current is less than 2.5  $\mu$ A.

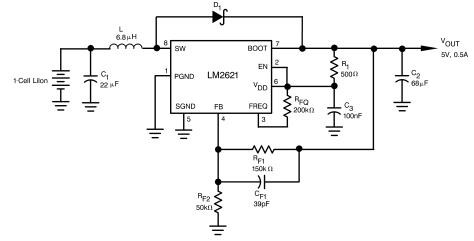
The LM2621 is available in a VSSOP-8 package. This package uses half the board area of a standard 8-pin SOIC and has a height of just 1.09 mm.

#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)			
LM2621	VSSOP (8)	3.00 mm x 3.00 mm			

(1) For all available packages, see the orderable addendum at the end of the datasheet.





2

## Table of Contents

1	Feat	tures 1
2	Арр	lications 1
3	Des	cription1
4	Rev	ision History 2
5	Pin	Configuration and Functions 3
6	Spe	cifications 3
	6.1	Absolute Maximum Ratings 3
	6.2	Recommended Operating Conditions 4
	6.3	Thermal Information 4
	6.4	Electrical Characteristics 4
	6.5	Typical Characteristics 5
7	Deta	ailed Description8
	7.1	Overview
	7.2	Functional Block Diagram 8
	7.3	Feature Description8
	7.4	Device Functional Modes9

## 4 Revision History

#### Changes from Revision C (November 2012) to Revision D

 Added Pin Configuration and Functions section, Handling Rating table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section

- 8 Application and Implementation ...... 10 8.1 Application Information..... 10 8.2 Typical Applications ..... 10 9 Power Supply Recommendations ...... 15 10 Layout...... 15 10.1 Layout Guidelines ..... 15 10.2 Layout Example ..... 15 Device and Documentation Support ...... 16 11 11.2 Documentation Support ..... 16 11.3 Community Resources...... 16 11.4 Trademarks ..... 16 Electrostatic Discharge Caution ...... 16 11.5 Glossary ...... 16 11.6

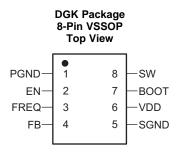
Texas Instruments

www.ti.com



#### LM2621 SNVS033D-MAY 2004-REVISED NOVEMBER 2015

## 5 Pin Configuration and Functions



#### **Pin Functions**

PIN	PIN		DESCRIPTION	
NAME	NO.	TYPE <sup>(1)</sup>	DESCRIPTION	
PGND	1	GND	ower Ground	
EN	2	I	Active-Low Shutdown Input	
FREQ	3	A	quency Adjust. An external resistor connected between this pin and Pin 6 (V <sub>DD</sub> ) sets the switching quency of the LM2621.	
FB	4	Α	utput Voltage Feedback	
SGND	5	GND	gnal Ground	
V <sub>DD</sub>	6	PWR	ower Supply for Internal Circuitry	
BOOT	7	PWR	potstrap Supply for the Gate Drive of Internal MOSFET Power Switch	
SW	8	PWR	Drain of the Internal MOSFET Power Switch	

(1) I = Input, O = Output, PWR = Power, GND = Ground, A = Analog

## 6 Specifications

#### 6.1 Absolute Maximum Ratings

See (1)(2)

	MIN	MAX	UNIT
SW Pin Voltage	-0.5	14.5	V
BOOT, V <sub>DD</sub> , EN and FB Pins	-0.5	10	V
FREQ Pin		100	μA
Power Dissipation ( $T_A=25^{\circ}C$ ) <sup>(3)</sup>		500	mW
T <sub>Jmax</sub> <sup>(3)</sup>		150	°C
Lead Temp. (Soldering, 5 sec)		260	°C
Storage temperature, T <sub>stg</sub>	-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.

(3) The maximum power dissipation must be derated at elevated temperatures and is dictated by T<sub>jmax</sub> (maximum junction temperature), θ<sub>JA</sub> (junction to ambient thermal resistance), and T<sub>A</sub> (ambient temperature). The maximum allowable power dissipation at any temperature is P<sub>dmax</sub> = (T<sub>jmax</sub> - T<sub>A</sub>)/ θ<sub>JA</sub> or the number given in the Absolute Maximum Ratings, whichever is lower.

SNVS033D-MAY 2004-REVISED NOVEMBER 2015

## 6.2 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	NOM MAX	UNIT
V <sub>DD</sub>	2.5	5	V
FB	0	V <sub>DD</sub>	V
EN	0	V <sub>DD</sub>	V
BOOT	0	10	V
Ambient Temperature, T <sub>A</sub>	-40	85	°C

#### Thermal Information 6.3

	THERMAL METRIC <sup>(1)</sup>	DGK (VSSOP)	UNIT
		8 PINS	
$R_{\thetaJA}$	Junction-to-ambient thermal resistance <sup>(2)</sup>	160	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	52.7	°C/W
$R_{ extsf{ heta}JB}$	Junction-to-board thermal resistance	80.1	°C/W
Ψυτ	Junction-to-top characterization parameter	5.5	°C/W
ΨЈВ	Junction-to-board characterization parameter	78.8	°C/W
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

The maximum power dissipation must be derated at elevated temperatures and is dictated by T<sub>jmax</sub> (maximum junction temperature), (2) θ<sub>JA</sub> (junction to ambient thermal resistance), and T<sub>A</sub> (ambient temperature). The maximum allowable power dissipation at any temperature is  $P_{dmax} = (T_{jmax} - T_A)/\theta_{JA}$  or the number given in the Absolute Maximum Ratings, whichever is lower.

## 6.4 Electrical Characteristics

Unless otherwise specified:  $V_{DD} = V_{OUT} = 3.3 \text{ V}$ ,  $T_J = 25^{\circ}\text{C}$ .

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>IN_ST</sub>	Minimum Start-Up Supply	I <sub>LOAD</sub> = 0 mA		1.1		V
	Voltage <sup>(1)</sup>	$I_{LOAD} = 0 \text{ mA}, -40^{\circ}\text{C} \text{ to } 85^{\circ}\text{C}$			1.2	v
$V_{IN\_OP}$	Minimum Operating Supply Voltage (once started)	$I_{LOAD} = 0 \text{ mA}$		0.65		V
$V_{\text{FB}}$	FB Pin Voltage			1.24		V
		-40°C to 85°C	1.2028		1.2772	v
V <sub>OUT_MAX</sub>	Maximum Output Voltage			14		V
V <sub>HYST</sub>	Hysteresis Voltage <sup>(2)</sup>			30		m)/
		–40°C to 85°C			45	mV
η	Efficiency	V <sub>IN</sub> = 3.6 V; V <sub>OUT</sub> = 5 V; I <sub>LOAD</sub> = 500 mA		87%		
		V <sub>IN</sub> = 2.5 V; V <sub>OUT</sub> = 3.3 V; I <sub>LOAD</sub> = 200 mA		87%		
D	Switch Duty Cycle			70%		
		−40°C to 85°C	60%		80%	
I <sub>DD</sub>	Operating Quiescent	FB Pin > 1.3 V; EN Pin at V <sub>DD</sub>		80		۵
	Current <sup>(3)</sup>	FB Pin > 1.3 V; EN Pin at V <sub>DD</sub> , -40°C to 85°C			110	μA
I <sub>SD</sub>	Shutdown Quiescent Current <sup>(4)</sup>	$V_{\text{DD}},$ BOOT and SW Pins at 5.0 V; EN Pin < 200 mV		0.01		
		$V_{DD},$ BOOT and SW Pins at 5.0 V; EN Pin < 200 mV, –40°C to 85°C			2.5	μA
I <sub>CL</sub>	Switch Peak Current Limit			2.85		А

(1)

Output in regulation,  $V_{OUT} = V_{OUT (NOMINAL)} \pm 5\%$ This is the hysteresis value of the internal comparator used for the gated-oscillator control scheme. (2)

(3)This is the current into the V<sub>DD</sub> pin.

This is the total current into pins V<sub>DD</sub>, BOOT, SW and FREQ. (4)

4 Submit Documentation Feedback



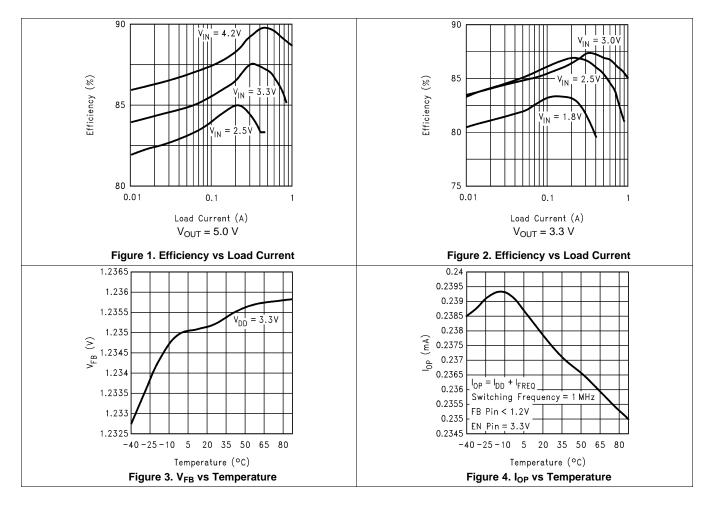
## **Electrical Characteristics (continued)**

Unless otherwise specified:  $V_{DD} = V_{OUT} = 3.3 \text{ V}, T_J = 25^{\circ}\text{C}.$ 

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
R <sub>DS_ON</sub>	MOSFET Switch On Resistance			0.17		Ω	
ENABLE	ENABLE SECTION						
V <sub>EN_LO</sub>	EN Pin Voltage Low <sup>(5)</sup>	-40°C to 85°C			$0.15V_{DD}$	V	
V <sub>EN_HI</sub>	EN Pin Voltage High <sup>(5)</sup>	-40°C to 85°C	0.7V <sub>DD</sub>			V	

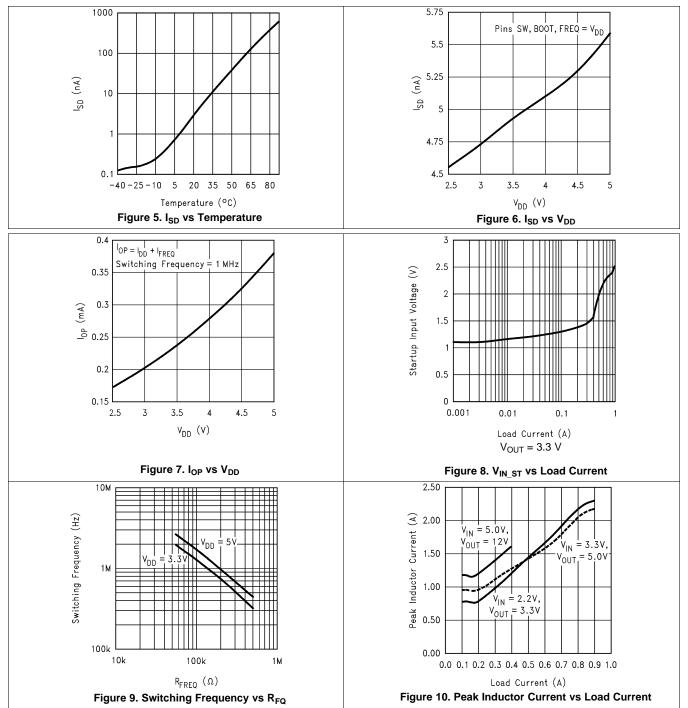
(5) When the EN pin is below  $V_{EN_LO}$ , the regulator is shut down; when it is above  $V_{EN_LHI}$ , the regulator is operating.

## 6.5 Typical Characteristics



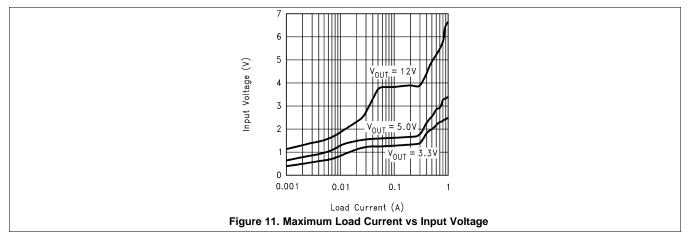


## **Typical Characteristics (continued)**





## **Typical Characteristics (continued)**



INSTRUMENTS www.ti.com

Texas

## 7 Detailed Description

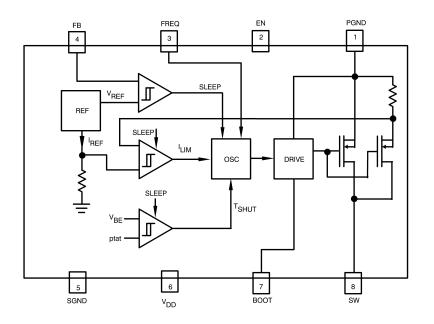
## 7.1 Overview

The LM2621 is designed to provide step-up DC-DC voltage regulation in battery-powered and low-input voltage systems. It combines a step-up switching regulator, N-channel power MOSFET, built-in current limit, thermal limit, and voltage reference in a single 8-pin VSSOP package *Pin Configuration and Functions*. The switching DC-DC regulator boosts an input voltage between 1.2 V and 14 V to a regulated output voltage between 1.24 V and 14 V. The LM2621 starts from a low 1.1-V input and remains operational down to 0.65 V.

This device is optimized for use in cellular phones and other applications requiring a small size, low profile, as well as low quiescent current for maximum battery life during stand-by and shutdown. A high-efficiency gated-oscillator topology offers an output of up to 1 A.

Additional features include a built-in peak switch current limit, and thermal protection circuitry.

## 7.2 Functional Block Diagram



### 7.3 Feature Description

#### 7.3.1 Gated Oscillator Control Scheme

A unique gated oscillator control scheme enables the LM2621 to have an ultra-low quiescent current and provides a high efficiency over a wide load range. The switching frequency of the internal oscillator is programmable using an external resistor and can be set between 300 kHz and 2 MHz.

This control scheme uses a hysteresis window to regulate the output voltage. When the output voltage is below the upper threshold of the window, the LM2621 switches continuously with a fixed duty cycle of 70% at the switching frequency selected by the user. During the first part of each switching cycle, the internal N-channel MOSFET switch is turned on. This causes the current to ramp up in the inductor and store energy. During the second part of each switching cycle, the diode to the output filter capacitor and the load. Thus when the LM2621 switches continuously, the output voltage starts to ramp up. When the output voltage hits the upper threshold of the window, the LM2621 stops switching completely. This causes the output voltage hits the lower threshold of the hysteresis window, the LM2621 starts switching continuously again causing the output voltage to ramp up towards the upper threshold. Figure 12 shows the switch voltage and output voltage waveforms.

Because of this type of control scheme, the quiescent current is inherently very low. At light loads the gated oscillator control scheme offers a much higher efficiency compared to the conventional PWM control scheme.



#### Feature Description (continued)

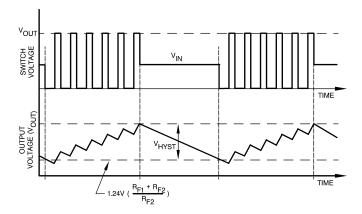


Figure 12. Typical Step-Up Regulator Waveforms

#### 7.3.2 Low Voltage Start-Up

The LM2621 can start-up from input voltages as low as 1.1 V. On start-up, the control circuitry switches the Nchannel MOSFET continuously at 70% duty cycle until the output voltage reaches 2.5 V. After this output voltage is reached, the normal step-up regulator feedback and gated oscillator control scheme take over. Once the device is in regulation it can operate down to a 0.65-V input, since the internal power for the IC can be bootstrapped from the output using the V<sub>DD</sub> pin.

#### 7.3.3 Output Voltage Ripple Frequency

A major component of the output voltage ripple is due to the hysteresis used in the gated oscillator control scheme. The frequency of this voltage ripple is proportional to the load current. The frequency of this ripple does not necessitate the use of larger inductors and capacitors however, since the size of these components is determined by the switching frequency of the oscillator which can be set up to 2 MHz using an external resistor.

#### 7.3.4 Internal Current Limit and Thermal Protection

An internal cycle-by-cycle current limit serves as a protection feature. This is set high enough (2.85 A typical, approximately 4 A maximum) so as not to come into effect during normal operating conditions. An internal thermal protection circuitry disables the MOSFET power switch when the junction temperature ( $T_J$ ) exceeds about 160°C. The switch is re-enabled when  $T_J$  drops below approximately 135°C.

### 7.4 Device Functional Modes

### 7.4.1 Shutdown

The LM2621 features a shutdown mode that reduces the quiescent current to less than a specified  $2.5-\mu$ A overtemperature. This extends the life of the battery in battery powered applications. During shutdown, all feedback and control circuitry is turned off. The regulator's output voltage drops to one diode drop below the input voltage. Entry into the shutdown mode is controlled by the active-low logic input pin EN (Pin 2). When the logic input to this pin pulled below 0.15 V<sub>DD</sub>, the device goes into shutdown mode. The logic input to this pin should be above 0.7 V<sub>DD</sub> for the device to work in normal step-up mode.

**NSTRUMENTS** 

FXAS

## 8 Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

## 8.1 Application Information

The LM2621 is primarily used as a Boost type step-up converter. The following section provides information regarding connection and component choices to build a successful boost converter. Examples of typical applications are also provided including a SEPIC step-up/step-down topology. More details on designing a SEPIC converter can be found here: SLYT309.

### 8.2 Typical Applications

#### 8.2.1 Step-Up DC-DC Converter Typical Application Using LM2621

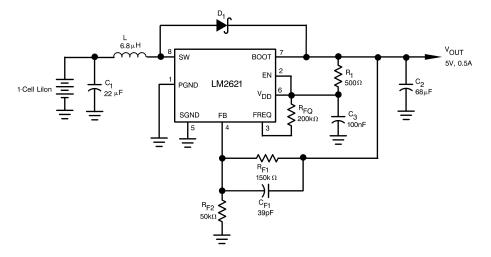


Figure 13. Typical Circuit

#### 8.2.1.1 Design Requirements

In order to successfully build an application, the designer should have the following parameters:

- Output voltage to set the feedback voltage divider and to assess the source for biasing the V<sub>DD</sub> pin.
- Input voltage range (min and max) to ensure safe operation within absolute max. rating of the IC.
- Output current to ensure that the system will not hit the internal peak current limit of the IC (2.85 A typical) during normal operation.

#### 8.2.1.2 Detailed Design Procedure

#### 8.2.1.2.1 Setting the Output Voltage

The output voltage of the step-up regulator can be set between 1.24 V and 14 V by connecting a feedback resistive divider made of  $R_{F1}$  and  $R_{F2}$ . The resistor values are selected as follows:

$$R_{F2} = R_{F1} / [(V_{OUT} / 1.24) - 1]$$

(1)

A value of 150 k $\Omega$  is suggested for R<sub>F1</sub>. Then, R<sub>F2</sub> can be selected using the above equation. A 39-pF capacitor (C<sub>F1</sub>) connected across R<sub>F1</sub> helps in feeding back most of the AC ripple at V<sub>OUT</sub> to the FB pin. This helps reduce the peak-to-peak output voltage ripple as well as improve the efficiency of the step-up regulator, because a set hysteresis of 30 mV at the FB pin is used for the gated oscillator control scheme.



#### Typical Applications (continued)

#### 8.2.1.2.2 Bootstrapping

When the output voltage ( $V_{OUT}$ ) is between 2.5 V and 5.0 V a bootstrapped operation is suggested. This is achieved by connecting the  $V_{DD}$  pin (Pin 6) to  $V_{OUT}$ . However if the  $V_{OUT}$  is outside this range, the  $V_{DD}$  pin should be connected to a voltage source whose range is between 2.5 V and 5 V. This can be the input voltage ( $V_{IN}$ ),  $V_{OUT}$  stepped down using a linear regulator, or a different voltage source available in the system. This is referred to as non-bootstrapped operation. The maximum acceptable voltage at the BOOT pin (Pin 7) is 10 V.

#### 8.2.1.2.3 Setting the Switching Frequency

The switching frequency of the oscillator is selected by choosing an external resistor ( $R_{FQ}$ ) connected between FREQ and  $V_{DD}$  pins. See Figure 9 for choosing the  $R_{FQ}$  value to achieve the desired switching frequency. A high switching frequency allows the use of very small surface mount inductors and capacitors and results in a very small solution size. A switching frequency between 300 kHz and 2 MHz is recommended.

#### 8.2.1.2.4 Inductor Selection

The LM2621's high switching frequency enables the use of a small surface mount inductor. A 6.8- $\mu$ H shielded inductor is suggested. The inductor should have a saturation current rating higher than the peak current it will experience during circuit operation (see Figure 10). Less than 100-m $\Omega$  ESR is suggested for high efficiency.

Open-core inductors cause flux linkage with circuit components and interfere with the normal operation of the circuit. They should be avoided. For high efficiency, choose an inductor with a high frequency core material, such as ferrite, to reduce the core losses. To minimize radiated noise, use a toroid, pot core or shielded core inductor. The inductor should be connected to the SW pin as close to the IC as possible. See Table 1 for a list of the inductor manufacturers.

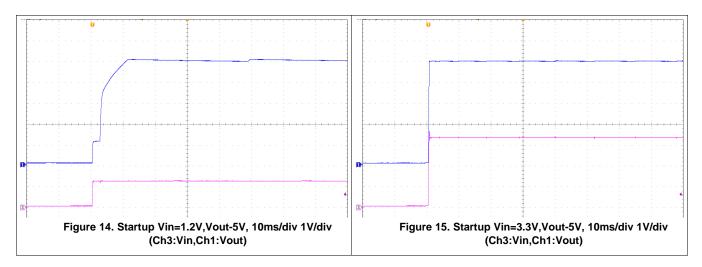
#### 8.2.1.2.5 Output Diode Selection

A Schottky diode should be used for the output diode. The forward current rating of the diode should be higher than the load current, and the reverse voltage rating must be higher than the output voltage. Do not use ordinary rectifier diodes, since slow switching speeds and long recovery times cause the efficiency and the load regulation to suffer. Table 1 shows a list of the diode manufacturers.

#### 8.2.1.2.6 Input and Output Filter Capacitors Selection

Tantalum chip capacitors are recommended for the input and output filter capacitors. A  $22-\mu$ F capacitor is suggested for the input filter capacitor. It should have a DC working voltage rating higher than the maximum input voltage. A  $68-\mu$ F tantalum capacitor is suggested for the output capacitor. The DC working voltage rating should be greater than the output voltage. Very high ESR values (> 3 $\Omega$ ) should be avoided.

### 8.2.1.3 Application Curves



## **Typical Applications (continued)**

## 8.2.2 5-V / 0.5-A Step-Up Regulator

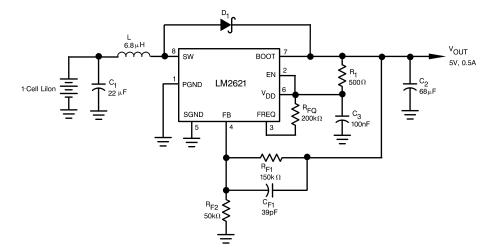


Figure 16. 5-V/0.5A Step-Up Regulator

#### 8.2.2.1 Design Requirements

Design requirement is the same to the typical application shown earlier. Components have been chosen that comply with the required maximum height. See *Design Requirements* for the design requirement and following sections for the detailed design procedure.

#### 8.2.2.2 Detailed Design Procedure

Follow the detailed design procedure in *Detailed Design Procedure*.

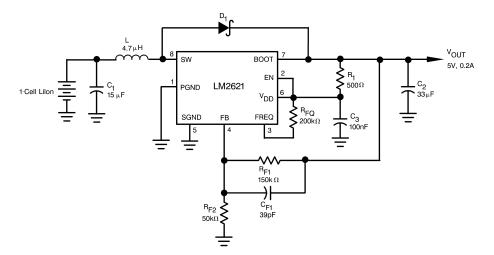


## **Typical Applications (continued)**

#### Table 1. Bill of Materials

	Manufacturer	Part Number
U1	ТІ	LM2621MM
C1	Vishay/Sprague	595D226X06R3B2T, Tantalum
C2	Vishay/Sprague	595D686X0010C2T, Tantalum
D1	Motorola	MBRS140T3
L	Coilcraft	DT1608C-682

#### 8.2.3 2-mm Tall 5-V / 0.2-A Step-Up Regulator for Low Profile Applications



#### Figure 17. 2-mm Tall 5-V/0.2A Step-Up Regulator for Low Profile Applications

#### 8.2.3.1 Design Requirements

Design requirement is the same to the typical application shown earlier. Components have been chosen that comply with the required maximum height. See *Design Requirements* for the design requirement and following sections for the detailed design procedure.

#### 8.2.3.2 Detailed Design Procedure

Follow the detailed design procedure in *Detailed Design Procedure*.

|--|

	Manufacturer	Part Number
U1	ТІ	LM2621MM
C1	Vishay/Sprague	592D156X06R3B2T, Tantalum
C2	Vishay/Sprague 592D336X06R3C2T, Tantalum	
D1	Motorola	MBRS140T3
L	Vishay/Dale	ILS-3825-03

#### 8.2.4 3.3-V / 0.5-A SEPIC Regulator

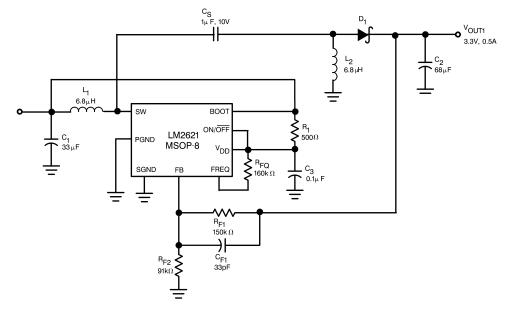


Figure 18. 3.3-V/0.5-A SEPIC Regulator

#### 8.2.4.1 Design Requirements

Design requirement for the SEPIC is similar to that of a boost but the current flowing through the switch is the addition of the current flowing through L1 and L2. As a result, the peak current through the main switch is  $I_{IN}+I_{OUT}+0.5xDeltaI_{L1}+0.5xDeltaI_{L2}$ . See SLYT309 for detail on the specific design requirement of a SEPIC converter.

### 8.2.4.2 Detailed Design Procedure

Follow the detailed design procedure in *Detailed Design Procedure*.

#### Table 3. Bill of Materials

	Manufacturer	Part Number	Description
U1	ТІ	LM2621MM	Low Input Voltage Regulator
C1	Sanyo	10CV220AX, SMT AL-Electrolytic	220 μF
C2	TDK	C2012X7R1C225M, MLCC	2.2 μF
C3	Vishay	VJ0603A331KXXAT	33 pF
C4	TDK	C3225X7R0J107MT	100 μF
C5, C6	Vishay	VJ0603Y104KXXAT	0.1 μF
D1	Philips	BAT54C	VR = 1V
D2	Vishay	MBRS120	1A / VR = 20V
L1, L2	Coilcraft	DO1813P-682HC	6.8 μH
R1	Vishay	CRCW08054990FRT6	499 Ω
R2	Vishay	CRCW08051503FRT6	150 kΩ
R3	Vishay	CRCW08053923FRT6	392 kΩ
R4	Vishay	CRCW08059092FRT6	90.9 kΩ



## 9 Power Supply Recommendations

The power line feeding the LM2621 should have low impedance. The input capacitor of the system should be placed as close to VIN as possible. If the power supply is very noisy, an additional bulk capacitor might be necessary in the system to ensure that clean power is delivered to the IC.

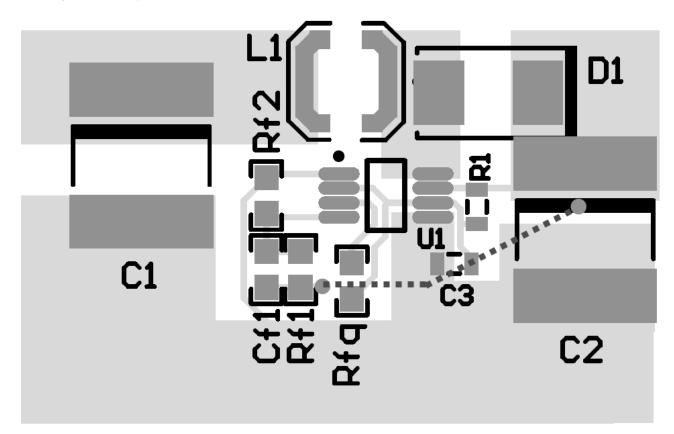
## 10 Layout

#### 10.1 Layout Guidelines

High switching frequencies and high peak currents make a proper layout of the PC board an important part of design. Poor design can cause excessive EMI and ground-bounce, both of which can cause malfunction and loss of regulation by corrupting voltage feedback signal and injecting noise into the control section.

Power components - such as the inductor, input and output filter capacitors, and output diode - should be placed as close to the regulator IC as possible, and their traces should be kept short, direct and wide. The ground pins of the input and output filter capacitors and the PGND and SGND pins of LM2621 should be connected using short, direct and wide traces. The voltage feedback network ( $R_{F1}$ ,  $R_{F2}$ , and  $C_{F1}$ ) should be kept very close to the FB pin. Noisy traces, such as from the SW pin, should be kept away from the FB and  $V_{DD}$  pins. The traces that run between  $V_{out}$  and the FB pin of the IC should be kept away from the inductor flux. Always provide sufficient copper area to dissipate the heat due to power loss in the circuitry and prevent the thermal protection circuitry in the IC from shutting the IC down.

### 10.2 Layout Example



## ••••• BOTTOM TRACE

#### Figure 19. LM2621 PCB Layout

TEXAS INSTRUMENTS

www.ti.com

## **11** Device and Documentation Support

#### **11.1 Device Support**

#### 11.1.1 Third-Party Products Disclaimer

TI'S PUBLICATION OF INFORMATION REGARDING THIRD-PARTY PRODUCTS OR SERVICES DOES NOT CONSTITUTE AN ENDORSEMENT REGARDING THE SUITABILITY OF SUCH PRODUCTS OR SERVICES OR A WARRANTY, REPRESENTATION OR ENDORSEMENT OF SUCH PRODUCTS OR SERVICES, EITHER ALONE OR IN COMBINATION WITH ANY TI PRODUCT OR SERVICE.

#### **11.2 Documentation Support**

#### 11.2.1 Related Documentation

For related documentation, see the following:

Designing DC/DC converters based on SEPIC topology, SLYT309

#### **11.3 Community Resources**

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E<sup>™</sup> Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support TI's Design Support** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

### 11.4 Trademarks

E2E is a trademark of Texas Instruments. All other trademarks are the property of their respective owners.

#### 11.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 11.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

## 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

#### **IMPORTANT NOTICE**

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products		Applications	
Audio	www.ti.com/audio	Automotive and Transportation	www.ti.com/automotive
Amplifiers	amplifier.ti.com	Communications and Telecom	www.ti.com/communications
Data Converters	dataconverter.ti.com	Computers and Peripherals	www.ti.com/computers
DLP® Products	www.dlp.com	Consumer Electronics	www.ti.com/consumer-apps
DSP	dsp.ti.com	Energy and Lighting	www.ti.com/energy
Clocks and Timers	www.ti.com/clocks	Industrial	www.ti.com/industrial
Interface	interface.ti.com	Medical	www.ti.com/medical
Logic	logic.ti.com	Security	www.ti.com/security
Power Mgmt	power.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video
RFID	www.ti-rfid.com		
OMAP Applications Processors	www.ti.com/omap	TI E2E Community	e2e.ti.com
Wireless Connectivity	www.ti.com/wirelessconnectivity		

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2015, Texas Instruments Incorporated